

Quartz Glass Crucible For Producing Silicon Crystals And Process For Producing Quartz Glass Crucible

Abstract

5 Quartz glass crucible for pulling a single crystal of silicon by the Czochralski method,
having an inside on which is arranged an inner layer of quartz glass which forms a
surface, wherein the inner layer is provided with a crystallization promoter which
upon heating of the quartz glass crucible during use as intended in crystal pulling
brings about a crystallization of quartz glass to form β -cristobalite, characterized in
10 that the concentration of synthetically obtained SiO_2 C at a distance d from the
surface is greater than the concentration of synthetically obtained SiO_2 at a distance
 d_2 from the surface, wherein d_2 is greater than d .

Fig. 1